TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MA2373FK

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

The TC7MA2373FK is a high performance CMOS octal D-type latch. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This 8 bit D-type latch is controlled by a latch enable input (LE) and output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

The 26 Ω series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

Features

- 26 Ω series resistors on outputs.
- Low voltage operation: $V_{CC} = 1.8 \sim 3.6 \text{ V}$
- High speed operation: $t_{pd} = 5.1 \text{ ns} (\text{max}) (V_{CC} = 3.0 \sim 3.6 \text{ V})$

$$t_{pd} = 6.1 \text{ ns} (max) (V_{CC} = 2.3 \sim 2.7 \text{ V})$$

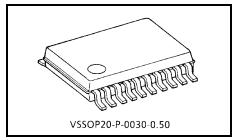
 $t_{pd} = 9.8 \text{ ns} (\text{max}) (\text{V}_{CC} = 1.8 \text{ V})$

- 3.6 V tolerant inputs and outputs.
- Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA} (min) (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 8 \text{ mA} \text{ (min)} (V_{CC} = 2.3 \text{ V})$

$$I_{OH}/I_{OL} = \pm 4 \text{ mA (min)} (V_{CC} = 1.8 \text{ V})$$

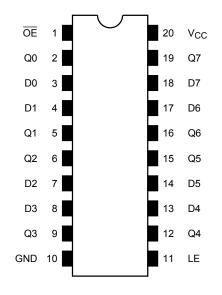
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$ Human body model $\geq \pm 2000 \text{ V}$
- Package: VSSOP (US)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (*)
 - *: To ensure the high-impedance state during power up or power down, $\overline{\mathsf{OE}}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.



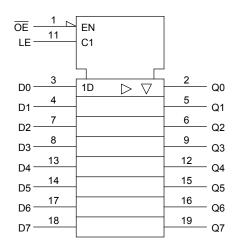
Weight: 0.03 g (typ.)

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Pin Assignment (top view)



IEC Logic Level



Truth Table

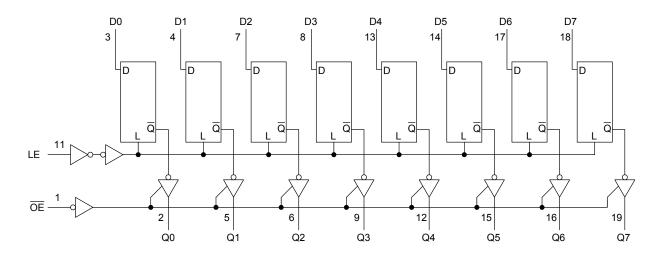
	Inputs	Outputs	
ŌĒ	LE	D	Outputs
н	х	х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

 Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Symbol Rating		
Power supply voltage	V _{CC}	-0.5~4.6	V	
DC input voltage	V _{IN}	-0.5~4.6	V	
DC output voltage	Vout	-0.5~4.6 (Note 2)	V	
De ouput voltage	VOUT	-0.5~V _{CC} + 0.5 (Note 3)		
Input diode current	I _{IK}	-50	mA	
Output diode current	I _{OK}	±50 (Note 4)	mA	
DC output current	I _{OUT}	±50	mA	
Power dissipation	PD	180	mW	
DC V _{CC} /ground current	I _{CC} /I _{GND}	±100	mA	
Storage temperature	T _{stg}	-65~150	°C	

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 2: Off-state
- Note 3: High or low state. IOUT absolute maximum rating must be observed.
- Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage	Vee	1.8~3.6	V
Supply vollage	V _{CC}	1.2~3.6 (Note 2)	v
Input voltage	VIN	-0.3~3.6	V
Output voltage	Vour	0~3.6 (Note 3)	V
Output voltage	Vout	0~V _{CC} (Note 4)	v
		±12 (Note 5)	
Output current	IOH/IOL	±8 (Note 6)	mA
		±4 (Note 7)	
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Note 2: Data retention only

- Note 3: Off-state
- Note 4: High or low state
- Note 5: $V_{CC} = 3.0 \sim 3.6 V$
- Note 6: $V_{CC} = 2.3 \sim 2.7 V$
- Note 7: $V_{CC} = 1.8 V$
- Note 8: $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$

Electrical Characteristics

DC Characteristics (Ta = -40~85°C, 2.7 V < V_{CC} \leq 3.6 V)

Characteristics		Symbol	Symbol Test Condition			Min	n Max	Unit
		Symbol			V _{CC} (V)	IVIITI		Unit
Input voltage	High level	VIH		_	2.7~3.6	2.0		V
input voltage	Low level	VIL		_	2.7~3.6		0.8	v
			I _{OH} = -100 μA	2.7~3.6	V _{CC} - 0.2	_		
	High level	VOH	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -6 \text{ mA}$	2.7	2.2		
				$I_{OH} = -8 \text{ mA}$	3.0	2.4		
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2		V
Low level	N.	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \ \mu A$	2.7~3.6	_	0.2		
			$I_{OL} = 6 \text{ mA}$	2.7	_	0.4		
	LOW IEVEI	V _{OL}	VIN = VIH OI VIL	$I_{OL} = 8 \text{ mA}$	3.0	_	0.55	
				$I_{OL} = 12 \text{ mA}$	3.0	_	0.8	
Input leakage curre	ent	l _{IN}	V _{IN} = 0~3.6 V	·	2.7~3.6		±5.0	μA
2 state output off c	tata aurrant	1	$V_{IN} = V_{IH} \text{ or } V_{IL}$		2.7~3.6		±10.0	
3-state output off-state current		loz	V _{OUT} = 0~3.6 V		2.7~3.0	_	±10.0	μA
Power off leakage	current	I _{OFF}	$V_{IN}, V_{OUT} = 0 \sim 3.6 V$		0	_	10.0	μA
			V _{IN} = V _{CC} or GND		2.7~3.6	_	20.0	
Quiescent supply of	current	Icc	$V_{CC} \stackrel{\scriptstyle \leq}{=} (V_{IN},V_{OUT}) \stackrel{\scriptstyle \leq}{=}$	\leq (V _{IN} , V _{OUT}) \leq 3.6 V		_	±20.0	μA
		∆lcc	$V_{IH} = V_{CC} - 0.6 V$ (pe	er input)	2.7~3.6	_	750	

DC Characteristics (Ta = -40~85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characteris	stics	Symbol	Test	Test Condition		Min	Мах	Unit			
Innutvaltage	High level	VIH		_	V _{CC} (V) 2.3~2.7	1.6		V			
Input voltage	Low level	VIL		_	2.3~2.7		0.7	V			
				I _{OH} = -100 μA	2.3~2.7	V _{CC} - 0.2	_				
	High level	Vон	VIN = VIH or VIL	$I_{OH} = -4 \text{ mA}$	2.3	2.0	_				
				$I_{OH} = -6 \text{ mA}$	2.3	1.8	_				
Output voltage				$I_{OH} = -8 \text{ mA}$	2.3	1.7	_	V			
			$V_{IN} = V_{IH} \text{ or } V_{IL}$	I _{OL} = 100 μA	2.3~2.7		0.2				
	Low level	V _{OL}		$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 6 \text{ mA}$	2.3	_	0.4	
				$I_{OL} = 8 \text{ mA}$	2.3		0.6				
Input leakage currer	nt	I _{IN}	V _{IN} = 0~3.6 V		2.3~2.7		±5.0	μA			
3-state output off-sta	i-state output off-state current I_{OZ} $V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OLIT} = 0~3.6 \text{ V}$			2.3~2.7	_	±10.0	μΑ				
Power off leakage c	urrent	IOFF	V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μA			
	urrant	1	$V_{IN} = V_{CC}$ or GND		2.3~2.7		20.0				
Quiescent supply cu	Inent	Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3$	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$			±20.0	μA			

DC Characteristics (Ta = -40~85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test Condition			Min	Max	Unit				
Characteri	51103	Gymbol	10310	Test Condition		IVIIII	Max	Offic				
Input voltage	High level	VIH		_	1.8~2.3	$0.7 \times V_{CC}$		V				
input voltage	Low level	VIL		_	1.8~2.3	_	$0.2 \times V_{CC}$	v				
	High level	Vон	VIN = VIH or VIL	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_					
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	V				
	Low level	Vol	VIN = VIH or VIL	I _{OL} = 100 μA	1.8	_	0.2					
	LOWIEVEI	VOL		$I_{OL} = 4 \text{ mA}$	1.8		0.3					
Input leakage curren	nt	I _{IN}	$V_{IN} = 0 \sim 3.6 V$		1.8		±5.0	μA				
3-state output off-sta	ate current	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0~3.6 \text{ V}$						1.8		±10.0	μA
Power off leakage c	urrent	I _{OFF}	$V_{IN}, V_{OUT} = 0 \sim 3.6 \text{ V}$		V _{IN} , V _{OUT} = 0~3.6 V		V _{IN} , V _{OUT} = 0~3.6 V		0		10.0	μA
Quiescent supply cu	urrent		V _{IN} = V _{CC} or GND		1.8		20.0	μA				
Quicacent supply ct		Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8	_	±20.0	μA				

AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition		Min	Max	Unit
			$V_{CC}(V)$			
	t _{pLH}		1.8	1.5	9.8	
Propagation delay time (D-Q)	t _{pHL}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.1	ns
	P =		$\textbf{3.3}\pm\textbf{0.3}$	0.6	5.1	
	t _{pLH}		1.8	1.5	9.8	
Propagation delay time (LE-Q)	t _{pHL}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.3	ns
	фнг		$\textbf{3.3}\pm\textbf{0.3}$	0.6	5.1	
			1.8	1.5	9.8	
3-state output enable time	t _{pZL}	Figure 1, Figure 3	2.5 ± 0.2	0.8	6.5	ns
	t _p zн		$\textbf{3.3}\pm\textbf{0.3}$	0.6	5.0	
		Figure 1, Figure 3	1.8	1.5	7.7	
3-state output disable time	t _{pLZ}		2.5 ± 0.2	0.8	4.3	ns
	^t pHZ		3.3 ± 0.3	0.6	3.9	
			1.8	4.0	_	
Minimum pulse width (LE)	t _{w (H)}	Figure 1, Figure 2	2.5 ± 0.2	1.5		ns
			3.3 ± 0.3	1.5		
			1.8	2.5	_	
Minimum set-up time	ts	Figure 1, Figure 2	2.5 ± 0.2	1.5	_	ns
			3.3 ± 0.3	1.5	_	
			1.8	1.0	_	
Minimum hold time	t _h	Figure 1, Figure 2	2.5 ± 0.2	1.0		ns
			3.3 ± 0.3	1.0	_	
			1.8		0.5	
Output to output skew	t _{osLH}	(Note)	2.5 ± 0.2		0.5	ns
	t _{osHL}		3.3 ± 0.3		0.5	115
			J.J ± U.J	_	0.5	

For $C_L = 50 \text{ pF}$, add approximately 300 ps to the AC maximum specification.

Note: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$

Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0 \text{ ns}$, $C_L = 30 \text{ pF}$)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Тур.	Unit
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	0.15	
Quiet output maximum dynamic V_{OL}	V _{OLP}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	0.25	V
		$V_{IH} = 3.3 V, V_{IL} = 0 V$	(Note)	3.3	0.35	
	Volv	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	-0.15	v
Quiet output minimum dynamic V_{OL}		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	-0.25	
		$V_{IH} = 3.3 V, V_{IL} = 0 V$	(Note)	3.3	-0.35	
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note)	1.8	1.55	
Quiet output minimum dynamic V_{OH}	V _{OHV}	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note)	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note)	3.3	2.65	

Note: This parameter is guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition			Typ.	Unit
Characteristics	Symbol Test Condition			V _{CC} (V)	тур.	Unit
Input capacitance	C _{IN}	—		1.8, 2.5, 3.3	6	pF
Output capacitance	CO	_		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{IN} = 10 \text{ MHz}$ (Note)	1.8, 2.5, 3.3	20	pF

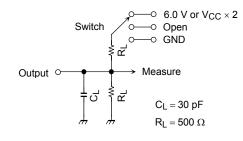
Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per bit)

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AC Test Circuit



Parameter	Switch			
t _{pLH} , t _{pHL}	Open			
t _{pLZ} , t _{pZL}	$ \begin{array}{ll} 6.0 \ V & @V_{CC} = 3.3 \pm 0.3 \ V \\ V_{CC} \times 2 & @V_{CC} = 2.5 \pm 0.2 \ V \\ @V_{CC} = 1.8 \ V \end{array} $			
t _{pHZ} , t _{pZH}	GND			



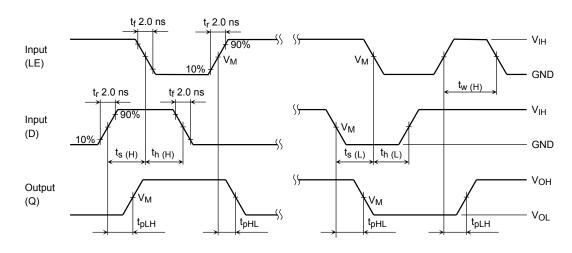


Figure 2 t_{pLH}, t_{pHL}, t_w, t_s, t_h

AC Waveform

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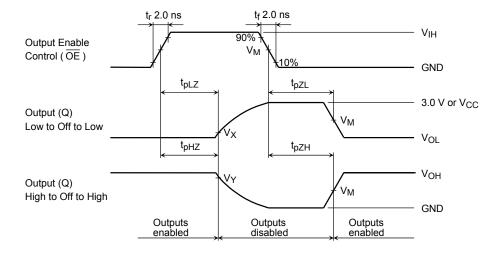


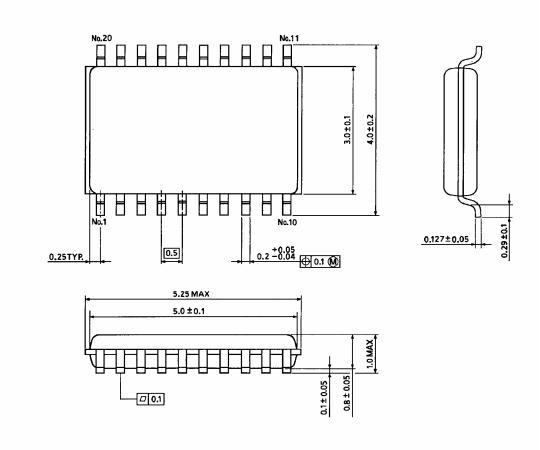
Figure 3	t _{pLZ} , t _{pHZ} , t _{pZL} , t _{pZH}
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Symbol	V _{CC}						
Symbol	$3.3\pm0.3~V$	$2.5\pm0.2~\text{V}$	1.8 V				
VIH	2.7 V	V _{CC}	V _{CC}				
VM	1.5 V	V _{CC} /2	V _{CC} /2				
Vx	V_{OL} + 0.3 V	V _{OL} + 0.15 V	V_{OL} + 0.15 V				
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V				

Package Dimensions



Unit : mm



Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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